

**ABSTRACT**

A method of forming an FSG film comprising the following steps. A structure is provided. An FSG film is formed over the structure by an HDP-CVD process under the following conditions: no Argon (Ar) - side sputter; SiF<sub>4</sub> flow: from about 53 to 63 sccm; an N<sub>2</sub> flow: from about 25 to 35 sccm; and an RF power to provide a uniform plasma density.